

L Number	Hits	Search Text	DB	Time stamp	
11	0	((thermodynamic thermal) near3 equilibrium) near12 (constant steady-state steady stationary stationnary continuous continuously dc) near12 (voltage potential current power energy)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 09:09	2003/07/07 09:05
12	102	((thermodynamic thermal) near3 equilibrium) near12 (constant steady-state steady stationary stationnary continuous continuously dc) near12 (voltage potential current power energy)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 09:09	
-	257	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film) and dielectric and semiconductor and electrode	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 09:05	
-	17	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film) and dielectric and semiconductor adj (layer or film) and ((second or top or cathode) near1 electrode)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 21:49	
-	39	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film) and dielectric and semiconductor adj (layer or film or substrate) and ((second or top or cathode) near1 electrode)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 21:50	
-	7	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film) and dielectric and semiconductor adj (layer or film or substrate) and ((second or top or cathode) near1 electrode) and (metal near2 (dopant or doped) or metal-doped or metal-dopant)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 21:55	
-	62	(tan or tantalum adj nitride) and (insulator or dielectric or glass) and semiconductor and ((cathode or upper or top) near3 electrode) and light-emitting	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 22:41	
-	18	depletion adj region near12 doping adj profile	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 22:41	
-	347	metal-doped	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:20	
-	19	metal-doped and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:21	
-	12	metal-doped and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:35	
-	3	metal-doped and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode) and ohmic adj contact	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:22	
-	109	(metal-doped or conducting adj polymer) and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:36	

-	23	(metal-doped or conducting adj polymer) and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode) and (multi-layer\$3 or laminat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:41
-	0	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near1 dop\$3 near3 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and (multi-layer\$3 or laminat\$3) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:46
-	0	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and (multi-layer\$3 or laminat\$3) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:47
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:49
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:53
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 10:55
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 10:56
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 10:57
-	7	((doped or doping) near2 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:40

-	8	((doped or doping or dopant) near3 (polyacetylene or ployimide or polyethylene or polyaniline)) near6 (conductivity or resistivity)) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:43
-	8	((doped or doping or dopant) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity)) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:44
-	1	((metal near2 (doped or doping or dopant)) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity)) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:46
-	2	p-type adj polyacetylene with semiconductor.ti,ab.	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:47
-	10	superlattice.ti,ab. and (jfet or junction adj field adj effect adj transistor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 14:56
-	187	superlattice.ti,ab. and (fet or field adj effect adj transistor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 14:56
-	0	((metal near5 insulat\$3) near5 superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 14:58
-	48	(superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab. and (aluminum or tungsten or copper or tantalum or molybdenum or metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 15:27
-	21	((superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab. and (aluminum or tungsten or copper or tantalum or molybdenum or metal)) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 16:19
-	11	257/658 and (jfet or fet or field adj effect transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 16:22
-	0	257/658 and (jfet or fet or field adj effect transistor) and superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 16:22
-	350	257/658	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 16:33
-	224	257/9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 16:39
-	435	257/15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 16:40

-	78	(257/28).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 17:13
-	1	("5250388").PN.	USPÄT	2002/03/13 18:54
-	1	("5049951").PN.	USPAT	2002/03/13 18:54
-	4	914103.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/03 15:31
-	4	914103.ap.	USPAT;	2003/07/04 12:36
-	0	monolayer near12 metal adj particle near12 nano\$7 and rectifier and semiconductor	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/04 12:37
-	0	monolayer near6 metal adj particle and rectifier and semiconductor	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/04 12:38
-	1	monolayer near6 rectifier and semiconductor	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/04 12:56
-	86	filed near6 national adj stage	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/04 12:57
-	3742	"[0001]" near16 International	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/04 13:49
-	64	tin adj dioxide near6 semiconductor	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/04 13:49
-	0	(rectifier Schottky) near6 (nanoparticle nano-particle)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPÄT;	2003/07/05 09:21

L Number	Hits	Search Text	DB	Time stamp
-	257	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/05 09:20
-	17	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor adj (layer or film) and ((second or top or cathode) near1 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 21:49
-	39	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor adj (layer or film or substrate) and ((second or top or cathode) near1 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 21:50
-	7	((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor adj (layer or film or substrate) and ((second or top or cathode) near1 electrode) and (metal near2 (dopant or doped) or metal-doped or metal-dopant)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 21:55
-	62	(tan or tantalum adj nitride) and (insulator or dielectric or glass) and semiconductor and ((cathode or upper or top) near3 electrode) and light-emitting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 22:41
-	18	depletion adj region near12 doping adj profile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/08 22:41
-	347	metal-doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:20
-	19	metal-doped and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:21
-	12	metal-doped and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:35
-	3	metal-doped and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:22
-	109	(metal-doped or conducting adj polymer) and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:36
-	23	(metal-doped or conducting adj polymer) and (257/\$6.ccls. or 438/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode) and (multi-layer\$3 or laminat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:41
-	0	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near1 dop\$3 near3 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and (multi-layer\$3 or laminat\$3) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:46

-	0	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and (multi-layer\$3 or laminat\$3) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:47
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:49
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/09 10:53
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 10:55
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 10:56
-	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 10:57
-	7	((doped or doping) near2 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:40
-	8	((doped or doping or dopant) near3 (polyacetylene or ployimide or polyethylene or polyaniline)) near6 (conductivity or resistivity) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:43
-	8	((doped or doping or dopant) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:44
-	1	((metal near2 (doped or doping or dopant)) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:46
-	2	p-type adj polyacetylene with semiconductor.ti,ab.	USPAT; EPO; JPO; IBM_TDB	2002/03/09 11:47

-	10	superlattice.ti,ab. and (jfet or junction adj field adj effect adj transistor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 14:56
-	187	superlattice.ti,ab. and (fet or field adj effect adj transistor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 14:56
-	0	((metal near5 insulat\$3) near5 superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 14:58
-	48	(superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab. and (aluminum or tungsten or copper or tantalum or molybdenum or metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 15:27
-	21	((superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab. and (aluminum or tungsten or copper or tantalum or molybdenum or metal)) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 16:19
-	11	257/658 and (jfet or fet or field adj effect transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 16:22
-	0	257/658 and (jfet or fet or field adj effect transistor) and superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 16:22
-	350	257/658	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 16:33
-	224	257/9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 16:39
-	435	257/15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 16:40
-	78	(257/28).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/09 17:13
-	1	("5250388").PN.	USPAT	2002/03/13 18:54
-	1	("5049951").PN.	USPAT	2002/03/13 18:54
-	4	914103.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/03 15:31
-	4	914103.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 12:36
-	0	monolayer near12 metal adj particle near12 nano\$7 and rectifier and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 12:37

-	0	monolayer near6 metal adj particle and rectifier and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 12:38
-	1	monolayer near6 rectifier and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 12:56
-	86	filed near6 national adj stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 12:57
-	3742	"[0001]" near16 International	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 13:49
-	64	tin adj dioxide near6 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/04 13:49
-	0	(rectifier Schottky) near6 (nanoparticle nano-particle)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/05 09:21